

# Field-enhanced electron capture by iron impurities in germanium

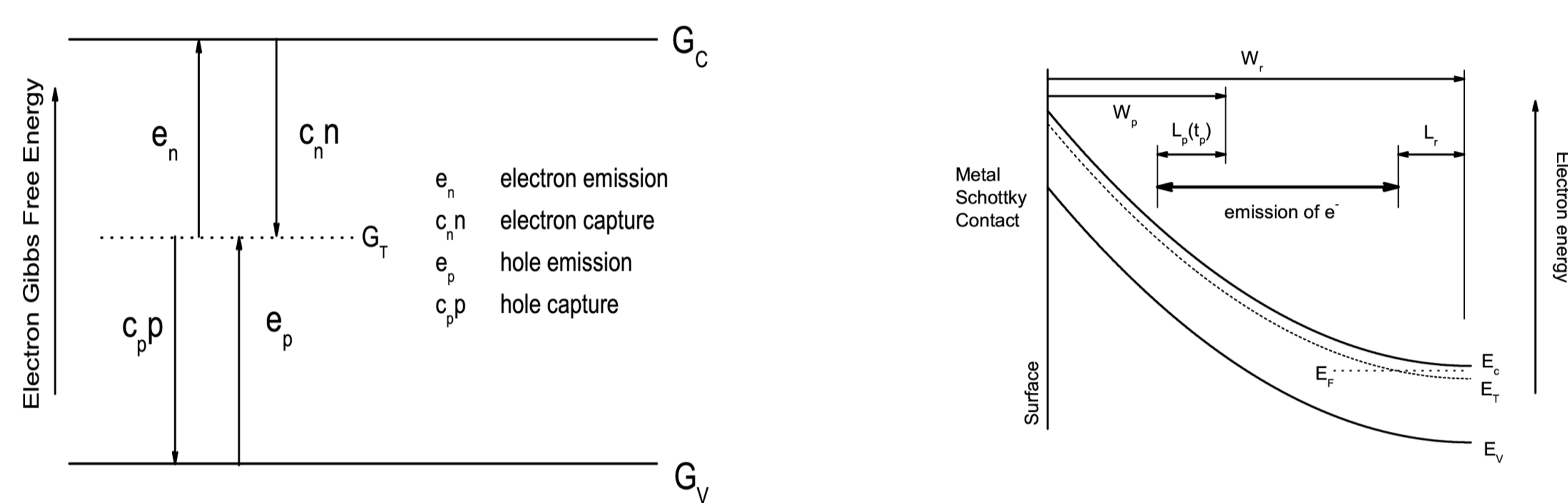
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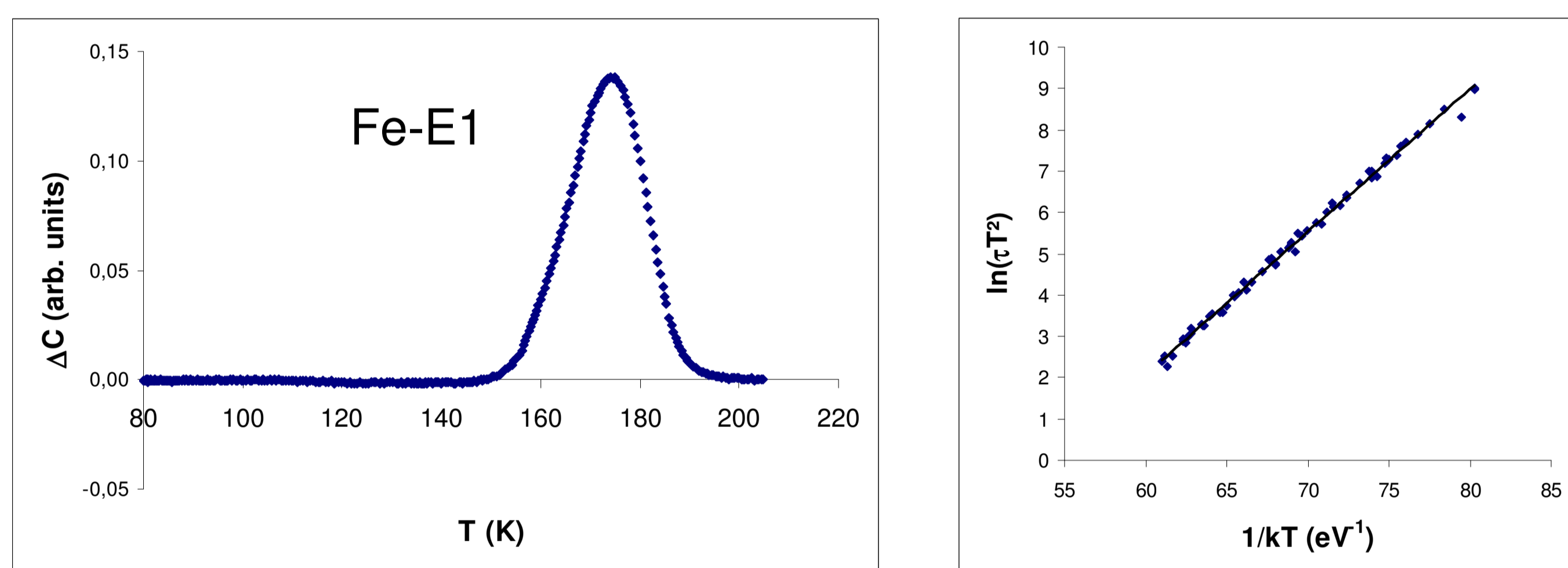
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## Conventional DLTS

### Capture versus Emission



### Analysis of the emission of e<sup>-</sup> from Fe<sup>2-/-</sup>



$$\frac{1}{\tau} = \sigma(\varepsilon) N_c v_{th} e^{-\frac{\Delta E(\varepsilon)}{kT}}$$

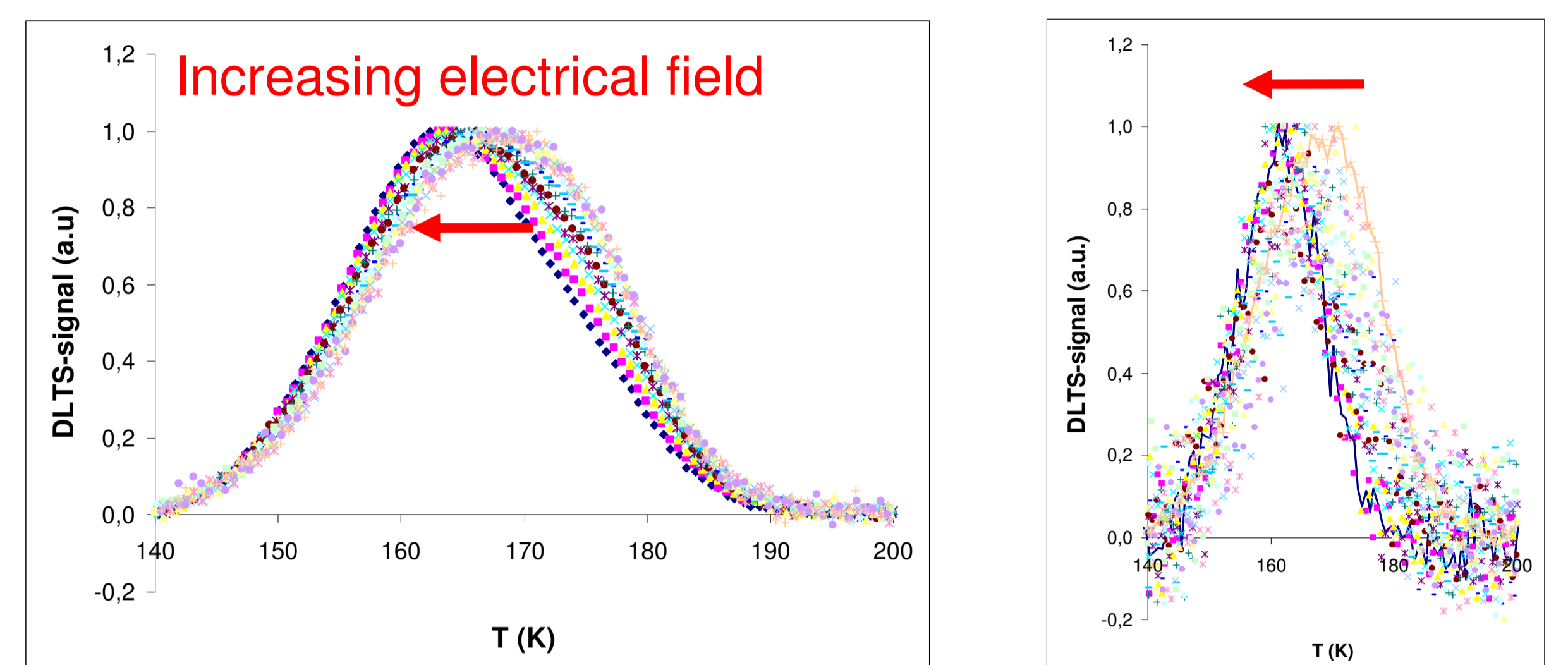
$$\ln(\tau T^2) = \frac{\Delta E(\varepsilon)}{k} \frac{1}{T} - \ln(K_T(\varepsilon))$$

Slope                      Intercept

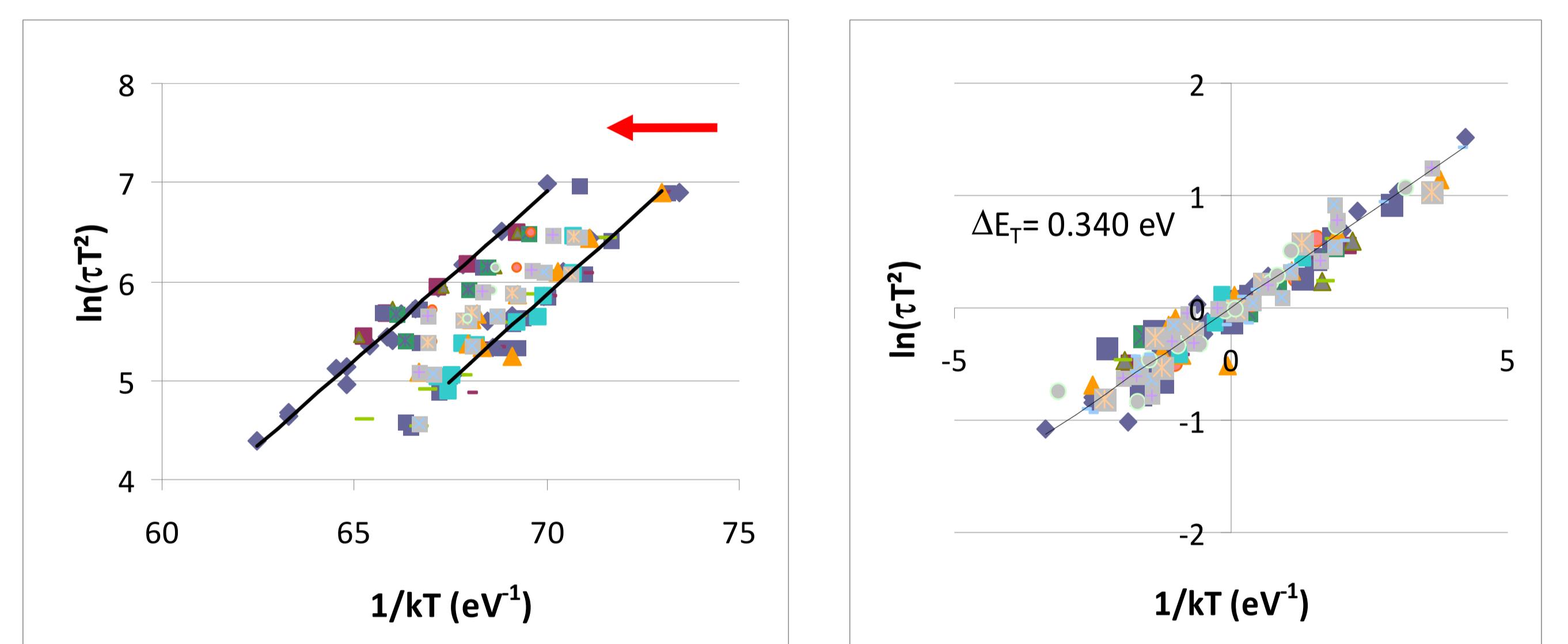
( $K_T, \Delta E$ ) signature of the electrical properties of a defect level

## Influence of electric field

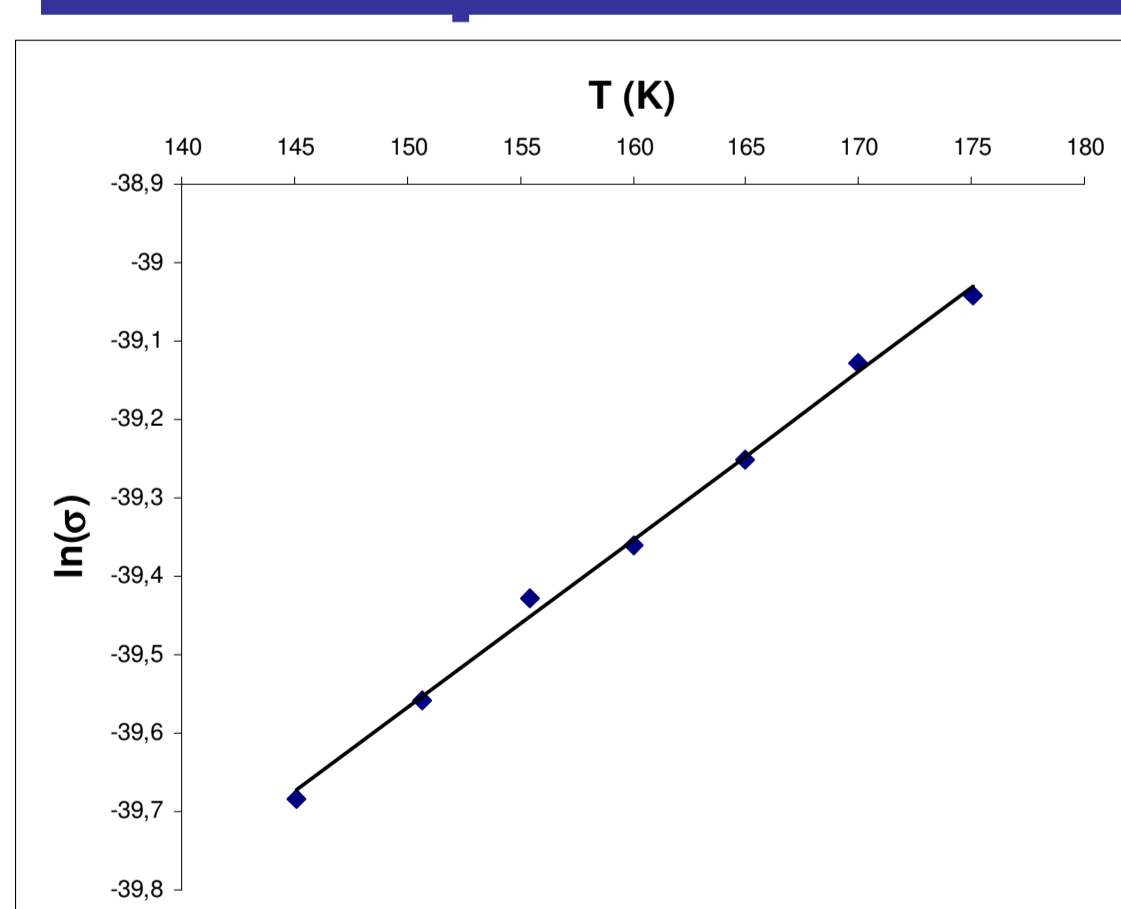
### Observed conventional DLTS peak shift



### Analysis of the measured time-constant

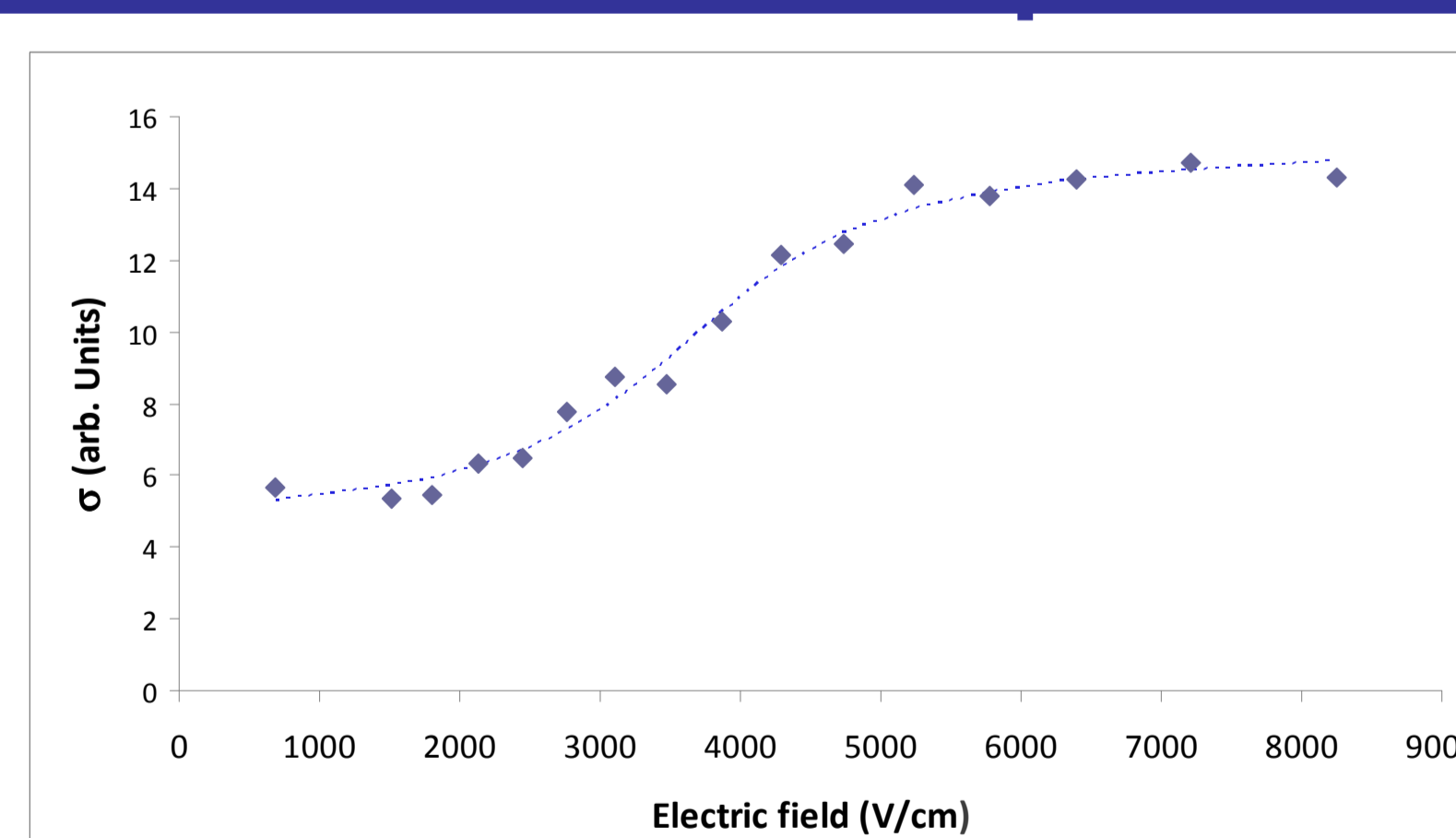


## Temperature and field dependence of capture cross-section



$$\sigma(T) = \sigma_{\infty} \exp\left(\frac{-\Delta E_{\sigma}}{k_B T}\right)$$

Capture in the neutral semiconductor



$$\sigma(\varepsilon) = A \tan^{-1}\left(\frac{\varepsilon - a}{b}\right) + B$$

Pre-exponential factor of emission from a region with electric field

## Conclusions

Data analysis revealed that an electric field affects the electron emission rate of Fe<sup>2-/-</sup> mainly through the pre-exponential factor, which is proportional to the capture cross section. An empirical electric field dependence of the electron capture cross section for a negatively charged iron impurity was deduced.